ERRATUM

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Erratum: Vertical GaN nanocolumns grown on graphene intermediated with a thin AlN buffer layer (Nanotechnology 30 015604)

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In the original article, on page 7, in the second sentence of the Conclusion, an error was introduced by the editors. The correct sentence should read: the AlN, grown using MEE technique, does not only serve as nucleation sites for the GaN nanocolumns, but it also provides considerable protection to the graphene from the N2 plasma source and in-plane strain generated by GaN nucleation.

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